

1200V, 25A, Trench FS II Fast IGBT

General Description:

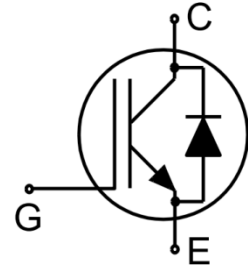
Using QIAOXIN's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low $V_{CE(sat)}$
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Inductive Cooking
- Soft Switching Applications



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
VCRR25TD120LT	TO-247	

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	50	A
	Collector Current @ $T_C = 100^\circ\text{C}$	25	A
I_{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	75	A
-	turn off safe operating area, $V_{CE}=1200\text{V}$, $T_j=150^\circ\text{C}$	75	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	25	A
I_{FM}	Diode Maximum Forward Current	75	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	365	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	183	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.41	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	0.86	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}C/W$

Electrical Characteristics ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
Static Characteristics						
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=1mA$	1200	--	--	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=1200V$	--	--	5	μA
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$	--	--	200	nA
$I_{GES(R)}$	Gate to Source Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$	--	--	200	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=25A, T_J=25^{\circ}C$	--	1.50	1.75	V
		$V_{GE}=15V, I_C=30A, T_J=25^{\circ}C$	--	1.60	--	V
		$V_{GE}=15V, I_C=25A, T_J=150^{\circ}C$	--	1.75	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}$	5.0	--	6.5	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE}=30V, V_{GE}=0V, f=1MHz$	--	2674	--	pF
C_{oes}	Output Capacitance		--	72	--	
C_{res}	Reverse Transfer Capacitance		--	59	--	
Q_g	Total Gate Charge	$V_{CC}=960V, I_C=25A, V_{GE}=15V$	--	146	--	nC
Q_{ge}	Gate to Emitter Charge		--	28	--	nC
Q_{gc}	Gate to Collector Charge		--	84	--	nC
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	$V_{CE}=600V, I_C=25A, V_{GE}=0/15V, R_g=5\Omega$ Inductive Load	--	19	--	ns
t_r	Rise Time		--	17	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	170	--	
t_f	Fall Time		--	18	--	
E_{on}	Turn-On Switching Loss		--	2.0	--	mJ
E_{off}	Turn-Off Switching Loss		--	1.5	--	
E_{ts}	Total Switching Loss		--	3.5	--	

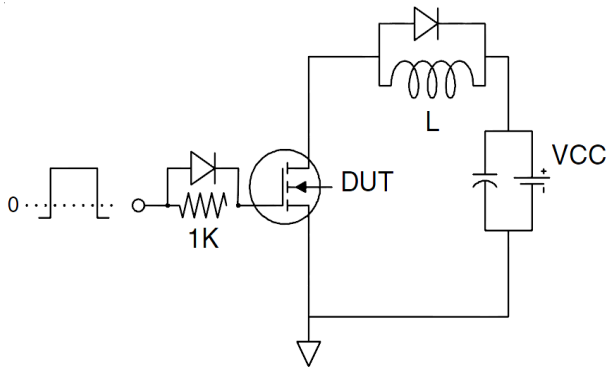
Electrical Characteristics of the Diode ($T_c=25^{\circ}C$ unless otherwise specified):

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{FM}	Diode Forward Voltage	$I_F=12.5A$	--	2.5	3.4	V
T_{rr}	Reverse Recovery Time	$I_F=12.5A, di/dt=200A/us$	--	120	--	ns
I_{RRM}	Diode Peak Reverse Recovery Current		--	12	--	A
Q_{rr}	Reverse Recovery Charge		--	0.72	--	μC

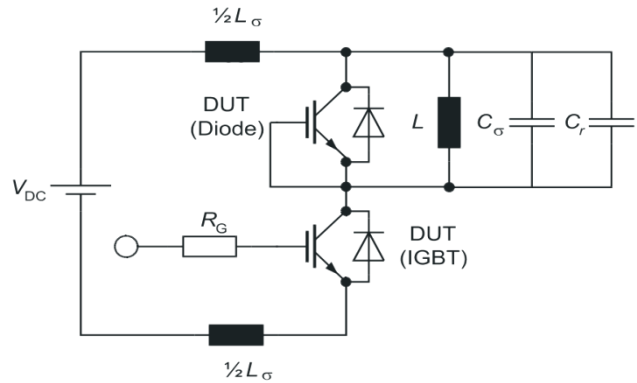
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$

Test Circuit

1) Gate Charge Test Circuit

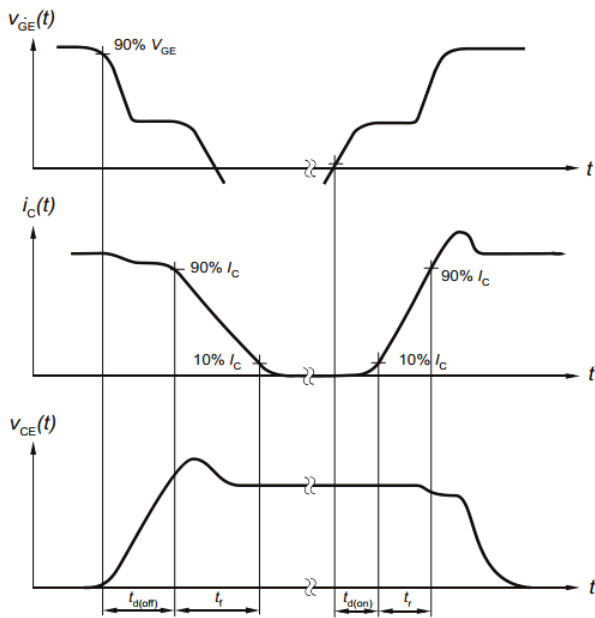


2) Switch Time Test Circuit

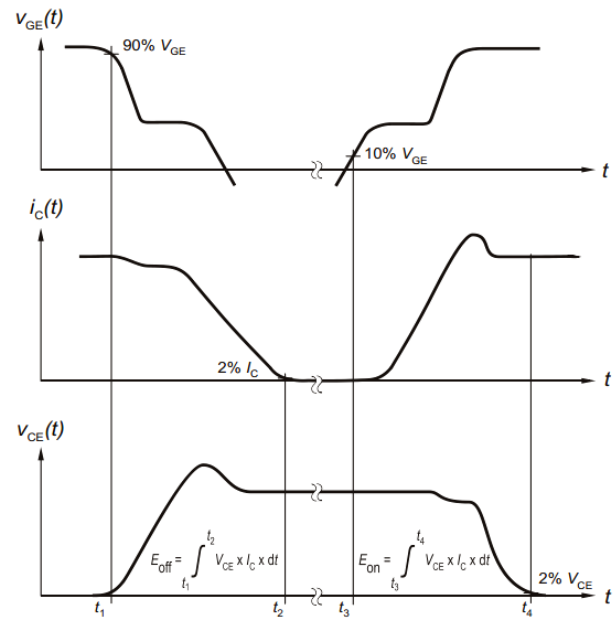


Switching characteristics

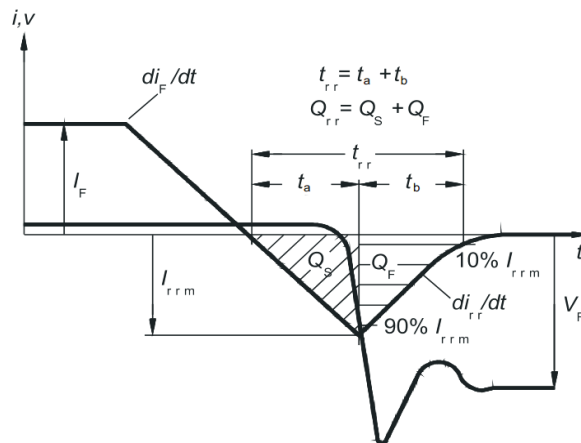
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

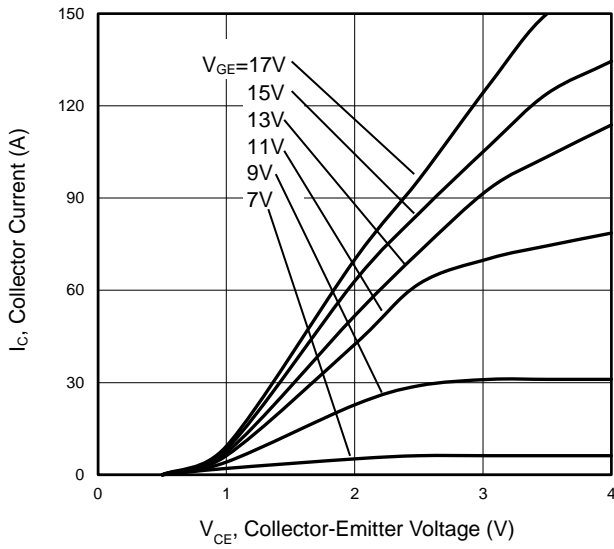


Figure 2 Transfer Characteristics

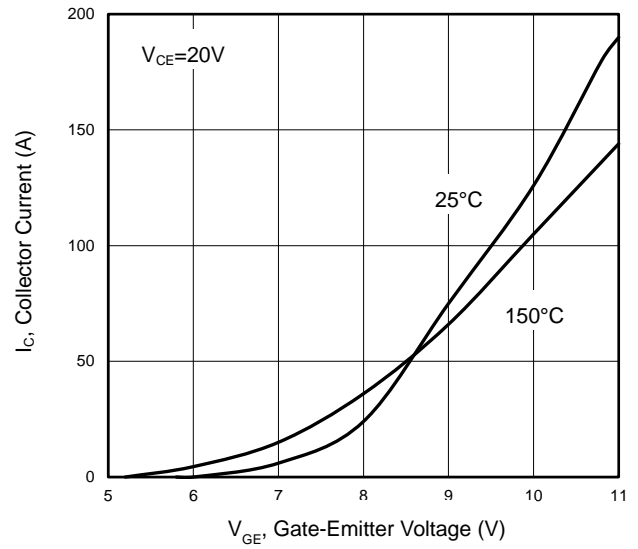


Figure 3 $V_{CE(sat)}$ vs. Case Temperature

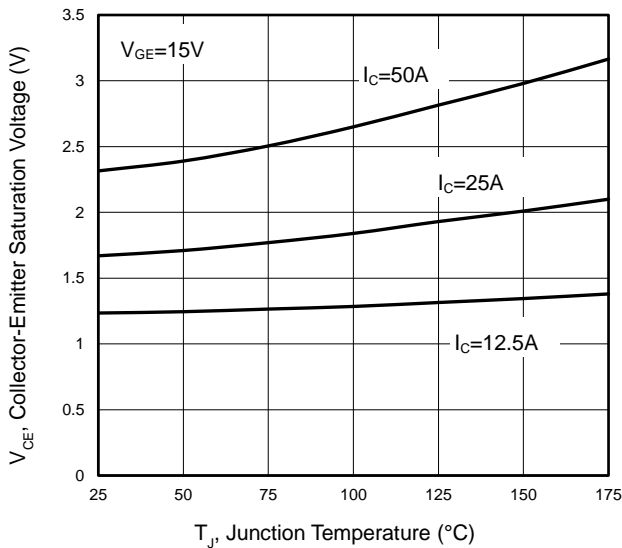


Figure 4 Saturation Voltage vs. V_{GE}

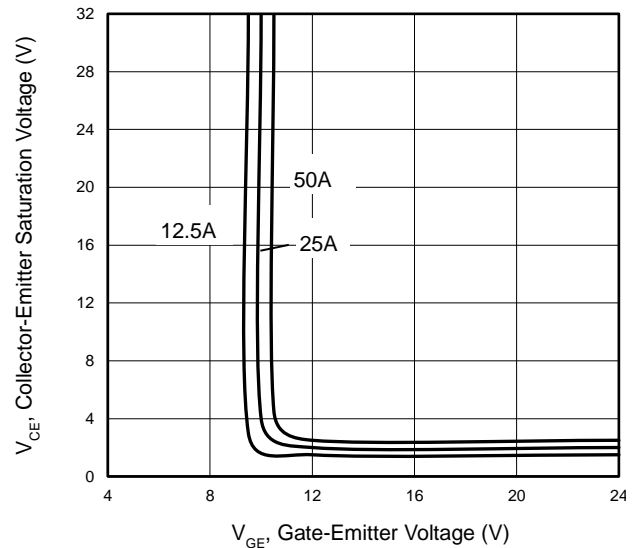


Figure 5 Capacitance Characteristics

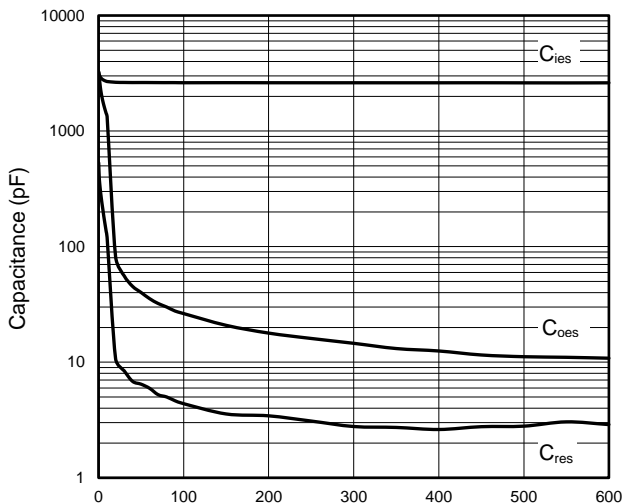
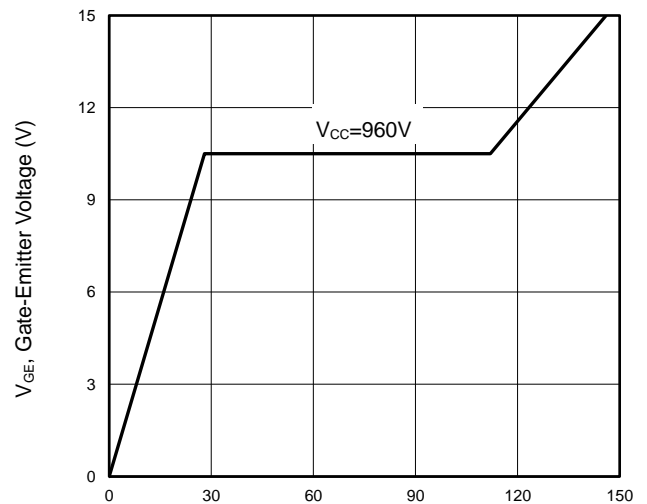
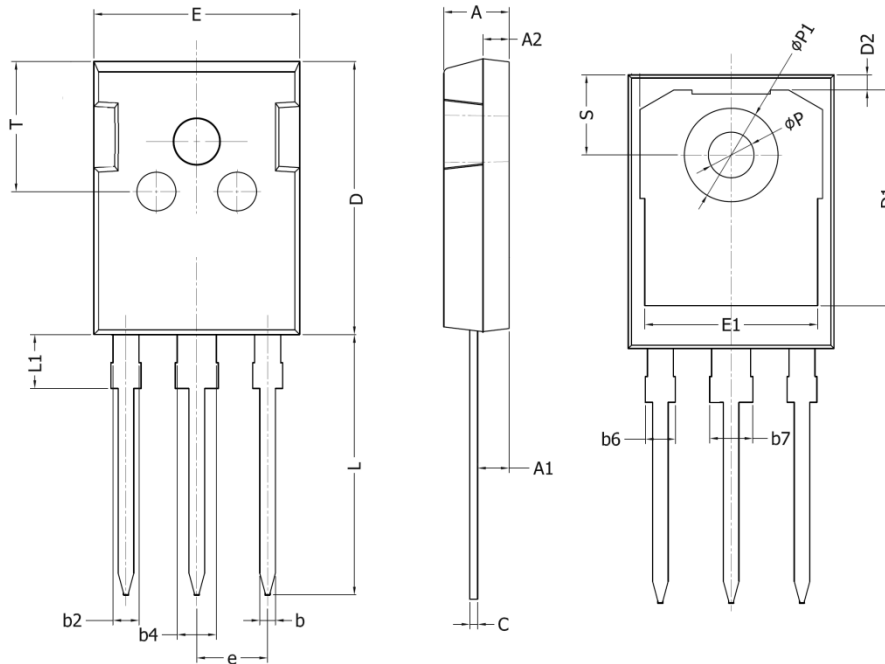


Figure 6 Gate Charge Wave Form



TO-247-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.9	2.1	0.075	0.083
b	1.16	1.26	0.046	0.050
b2	1.96	2.06	0.077	0.081
b4	2.96	3.06	0.117	0.120
b6	-	2.25	-	0.089
b7	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
e	5.436 BSC		0.214 BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
P	3.40	3.60	0.134	0.142
P1	7.00	7.40	0.276	0.291
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402

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